

## 650V 40A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	40A
V <sub>CE(sat) (Typ.)</sub>	1.65V
$P_D$	234W

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Low Switching Loss
- 3) Short Circuit Withstand Time 5µs
- 4) Built in Very Fast & Soft Recovery FRD (RFN Series)
- 5) Pb free Lead Plating; RoHS Compliant

## Applications

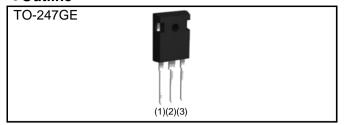
General Inverter

**UPS** 

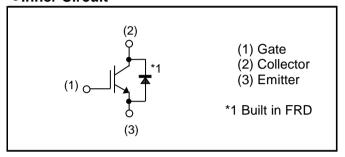
**Power Conditioner** 

Welder

#### Outline



#### ●Inner Circuit



Packaging Specifications

		Packaging	Tube	
		Reel Size (mm)	-	
	Typo	Tape Width (mm)	-	
	Type	Basic Ordering Unit (pcs)	600	
		Packing code	C13	
		Marking	RGT80TS65D	

## ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		V <sub>GES</sub>	±30	V
	T <sub>C</sub> = 25°C	I <sub>C</sub>	70	А
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	40	А
Pulsed Collector Current		I <sub>CP</sub> *1	120	А
Diode Forward Current	T <sub>C</sub> = 25°C	l <sub>F</sub>	40	А
	T <sub>C</sub> = 100°C	l <sub>F</sub>	20	А
Diode Pulsed Forward Current		I <sub>FP</sub> *1	120	А
Dower Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	234	W
Power Dissipation	T <sub>C</sub> = 100°C	P <sub>D</sub>	117	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

## ●Thermal Resistance

Parameter	Symbol	Values			Linit
Farameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.64	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.00	°C/W

# ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
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Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_C = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	ı	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, \ V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 27.6 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 40A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.65 2.15	2.1	V

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Linit			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2210	-		
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	87	-	pF	
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	36	-		
Total Gate Charge	Qg	V <sub>CE</sub> = 300V	-	79	-		
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 40A	-	21	-	nC	
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	29	-		
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	34	-		
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	56	-	ns	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	119	-		
Fall Time	t <sub>f</sub>	Inductive Load	-	55	-		
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 40A, V_{CC} = 400V$	-	34	-		
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_{G} = 10\Omega$	-	56	-	no	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	131	-	ns	
Fall Time	t <sub>f</sub>	Inductive Load	-	75	-		
		$I_C = 120A, V_{CC} = 520V$					
Reverse Bias Safe Operating Area RBS		$V_P = 650 V, V_{GE} = 15 V$	FULL SQUARE			-	
		$R_G = 50\Omega, T_j = 175^{\circ}C$					
		V <sub>CC</sub> ≦ 360V					
Short Circuit Withstand Time	t <sub>sc</sub>	V <sub>GE</sub> = 15V	5	-	-	μs	
		T <sub>j</sub> = 25°C					

## **•FRD Electrical Characteristics** (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Onit
Diode Forward Voltage	V <sub>F</sub>	$I_F = 20A$ $T_j = 25$ °C $T_j = 175$ °C	-	1.35 1.15	1.8	V
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F = 20A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 25^{\circ}C$	-	58	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		-	6.5	-	А
Diode Reverse Recovery Charge	$Q_{rr}$		-	0.21	-	μC
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A	-	236	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>	$V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	10.7	-	А
Diode Reverse Recovery Charge	$Q_{rr}$		-	1.36	-	μC

Fig.1 Power Dissipation vs. Case Temperature

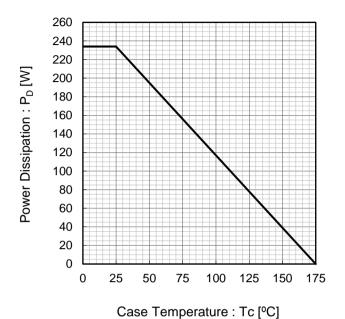
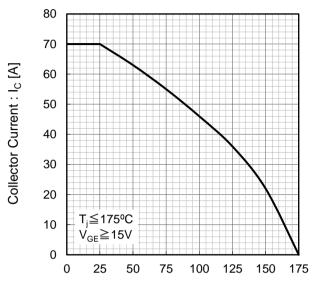


Fig.2 Collector Current vs. Case Temperature



Case Temperature : Tc [°C]

Fig.3 Forward Bias Safe Operating Area

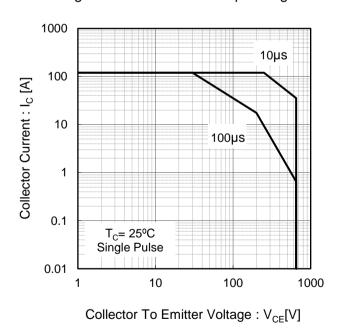
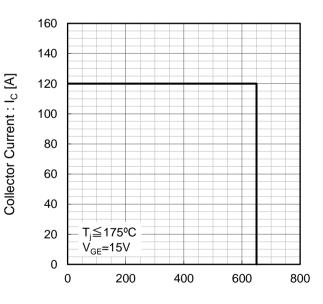


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.5 Typical Output Characteristics

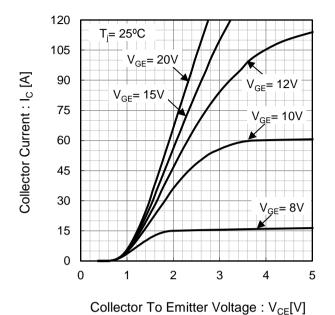
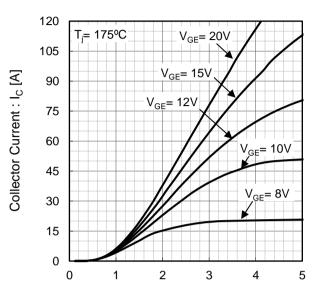


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

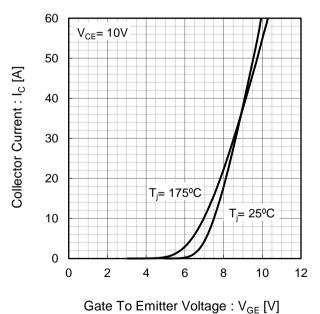
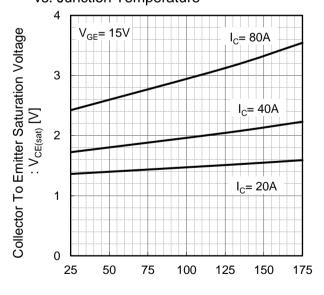
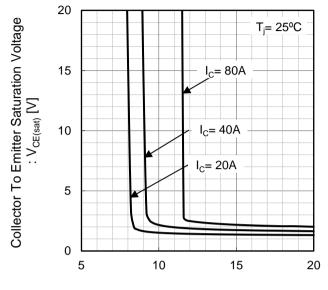


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



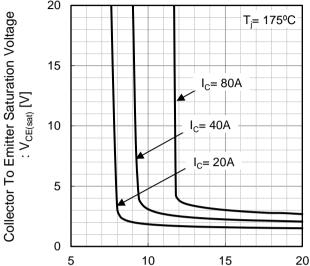
Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



vs. Gate To Emitter Voltage

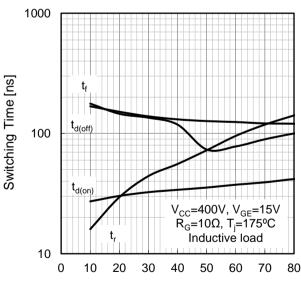
Fig.10 Typical Collector To Emitter Saturation Voltage



Gate To Emitter Voltage: V<sub>GE</sub> [V]

Gate To Emitter Voltage: V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance

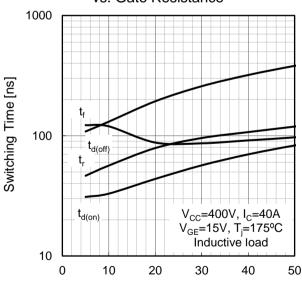
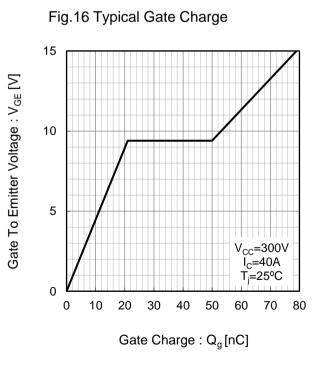


Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 Eoff 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 30 70 0 10 20 50 60 80 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=40A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage :  $V_{CE}[V]$ 



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Fig.17 Typical Diode Forward Current vs. Forward Voltage 120 105 Forward Current : I<sub>F</sub> [A] 90 75 60 45 30 = 175°C T<sub>i</sub>= 25°C 15 0 0.5 1.5 2 2.5 3 0

vs. Forward Current 400  $V_{CC}$ =400V di<sub>F</sub>/dt=200A/µs Reverse Recovery Time: t<sub>rr</sub> [ns] Inductive load 300 T<sub>i</sub>= 175°C 200 100 T<sub>i</sub>= 25°C 0 10 20 30 40 50 0 Forward Current : I<sub>F</sub> [A]

Fig.18 Typical Diode Reverse Recovery Time

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

Forward Voltage: V<sub>F</sub>[V]

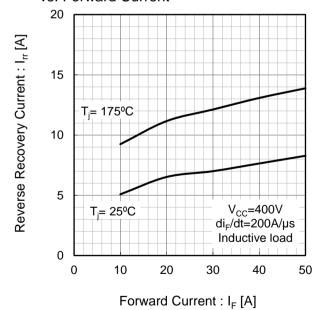
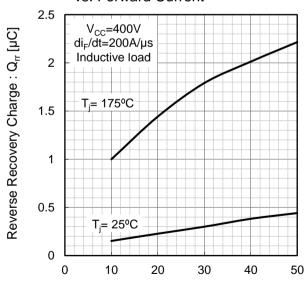
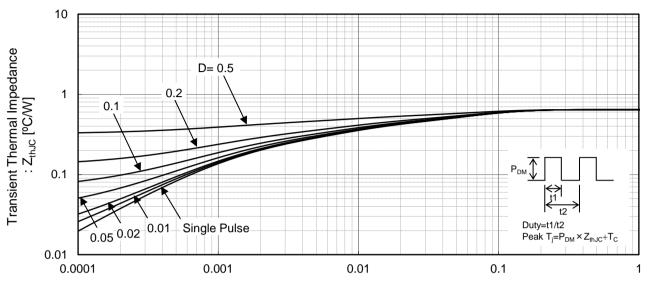


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



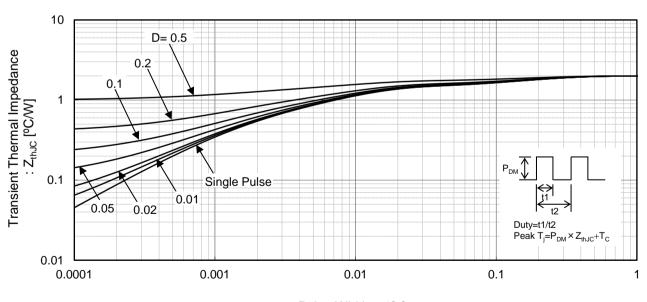
Forward Current : I<sub>F</sub> [A]

Fig.21 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

Fig.22 Diode Transient Thermal Impedance



## ●Inductive Load Switching Circuit and Waveform

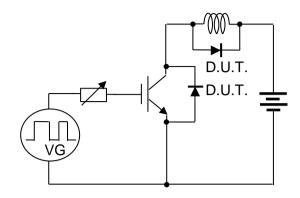


Fig.23 Inductive Load Circuit

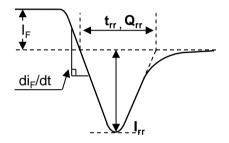


Fig.25 Diode Reverce Recovery Waveform

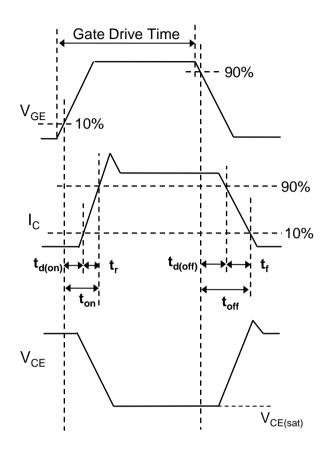


Fig.24 Inductive Load Waveform

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